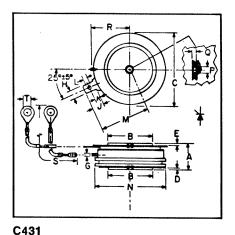
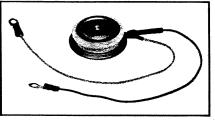


Phase Control SCR 450-600 Amperes Avg 500-1800 Volts





C431 Phase Control SCR 450-600 Amperes/500-1800 Volts

Description

Powerex Silicon Controlled Rectifiers (SCR) are designed for phase control applications. These are all-diffused, Press-Pak (Pow-R-Disc) devices employing the field-proven amplifying (di/namic) gate.

Features:

- Low On-State Voltage
- ☐ High di/dt
- High dv/dt
- Hermetic Packaging
- Excellent Surge and I²t Ratings

Applications:

- Power Supplies
- Battery Chargers
- Motor Control
- Light Dimmers
- □ VAR Generators

Ordering Information

Example: Select the complete six or seven digit part number you desire from the table – i.e. C431T1 is a 900 Volt, 600 Ampere Phase Control SCR.

	Volta ge		Current	
Туре	Vdrm Vrrm	Code	lī (avg)	Code
C431	50 0	E	450	2
	6 00	М	60 0	1
	70 0	S		
	8 00	N		
	90 0	Т		
	10 00	P		
	1100	PA		
	120 0	PB		
	13 00	PC		
	1400	PD		
	150 0 .	PE		
	16 00	PM		

Outline Drawing

	Inches		Millimeters		
Dimension s	Min.	Max.	Min.	Max.	
A	.56 0	.605	14.2 2	15.37	
В	.9 85	.995	25. 01	25.27	
С	1.60 0	1.650	40. 64	41.91	
D	.0 30		.76		
E	.04 0		1.01		
G	.057	.05 9	1.44	1.50	
Н	.18 6	.191	4.72	4.85	
J	.245	.25 5	6.22	6. 48	
ĸ	.115	.130	2.9 2	3.30	
L	.064	.07 0	1.62	1.78	
M		1.120		28.45	
N		1.585	-	40. 26	
Р	.135	.145	3.42	3. 68	
Q	.07 0	.084	1.77	2.13	
R		.875	—	22. 23	
S	12.219	12.34 3	310.3 6	313. 51	
T	.137	.153	3.47	3. 89	



\$

C431 Phase Control SCR 450-600 Amperes Avg/500-1800 Volts

Absolute Maximum Ratings

a da anti-anti-anti-anti-anti-anti-anti-anti-	Symbol	C4311	C4312	Units
RMS On-State Current	· IT(RMS)	9 50	70 0	Amperes
Average On-State Current	IT(av)	60 0	450	Amperes
Peak One-Cycle Surge (Non Repetitive) On-State Current (60Hz)	ITSM	8 000	6 500	Amperes
Peak One-Cycle Surge (Non-Repetitive) On-State Current (50Hz)	ITSM	73 00	59 50	Amperes
Critical Rate-of-Rise of On-State Current (Non-Repetitive)	di/dt	150	150	Amperes/µs
Critical Rate-of-Rise of On-State Current (Repetitive)	di/dt	100	100	Amperes/µs
I ² t (for Fusing), One Cycle at 60Hz	l²t	2.678 × 10⁵	1.76 × 10⁵	A ² sec
Peak Gate Power Dissipation	Р	20 0	20 0	Watts
Average Gate Power Dissipation	P _{G(av)}	5	5	Watts
Storage Temperature	T _{STG}	-40 to 150	-40 to 150	•C
Operating Temperature	Tj	-40 to 125	-40 to 125	° C
Mounting Force [®]		800-2500	800-2500	lb.
Mounting Force [®]		3.6-11.1	3.6-11.1	kN

 $\ensuremath{\textcircled{}}$ Consult recommended mounting procedures.

C431

Phase Control SCR 450-600 Amperes Avg/500-1800 Volts

Electrical and Thermal Characteristics

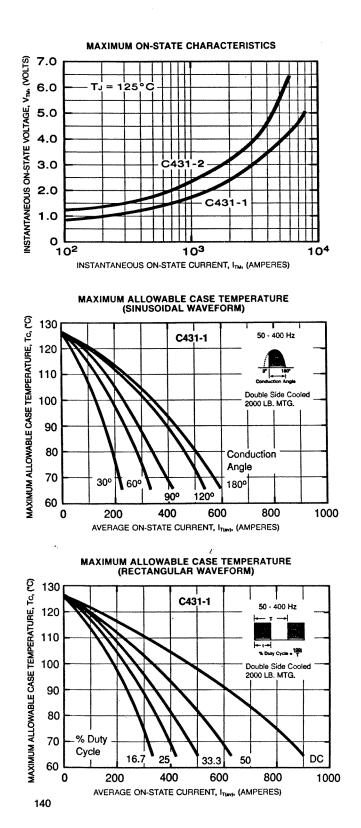
	Symbol	Test Conditions	C4311	C4312	Uni ts
Current—Conducting State Maximums Peak On-State Voltage	V _{TM}	I _{TM} = 3000A Peak, T _J = 25°C, Duty Cycle ≤ 0.01%	2.6 2	3.6	Volts
Voltage—Blocking State Maximums Forward Leakage, Peak	DRM	$T_J = 125^{\circ}C, V = V_{DRM}$	45	60	mA
Reverse Leakage, Peak	IRAM	$T_{J} = 125^{\circ}C, V = V_{BBM}$	45 60		mA
Switching Typical Turn-Off Time	t _q	$\begin{array}{l} T_{J}=125^{\circ}\text{C},\ I_{TM}=500\text{A};\\ V_{R}=50\text{V}\ \text{Min};\ V_{DRM}\ (\text{Reapplied});\\ dv/dt=20\text{V}/\mu\text{sec}\ (\text{linear});\\ \text{Commutation}\ di/dt=25\text{A}/\mu\text{sec};\\ \text{Repetition}\ \text{Rate}=1\text{pps};\ \text{Gate}\ \text{Bias}\\ \text{during}\ \text{Turn-Off}\ \text{Interval}=0\text{V},\ 100\Omega \end{array}$	200	75	μs ec
			C.4	31	
Typical Delay Time	ta	T _J = 25°C, I _T = 50A, Gate Supply: 20V, 20Ω, 0.1μsec rise time	.7		 μsec
Min. Critical dv/dt exponential to V _{DRM}	dv/ dt	$T_J = 125^{\circ}C, V_{DRM} = .8$ Rated, Gate Open	200		V/µs ec
Thermal and Mechanical Maximum Thermal Resistance, [©] double sided cooling Junction to Case (2000 lb force)	R _{elC}			.045	°C/Watt
Case to Sink, Lubricated (2000 lb force)	R _{ecs}		.045		°C/Watt
Gate—Maximum Parameters Gate Current to Trigger	l _{GT}	$V_{p} = 6Vdc, T_{J} = 25^{\circ}C, R_{L} = 3\Omega$	15		mA
Gate Voltage to Trigger	V _{GT}	$V_D = 6Vdc, \ N_J = 250, \ N_L = 502$ $T_J = -40 \text{ to } 125^{\circ}C, \ V_D = 6Vdc, \ R_L = 3\Omega$	5		Volts
Non-Triggering Gate Voltage Vo		$T_J = 125^{\circ}C$, Rated V_{DRM} , $R_L = 1000\Omega$.15		Volts
Peak Forward Gate Current	IGTM		1	0	Amperes
Peak Reverse Gate Voltage				5	Volts

0 Consult recommended mounting procedures.



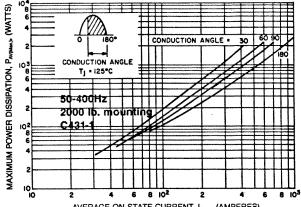
C431

Phase Control SCR 450-600 Amperes Avg/500-1800 Volts



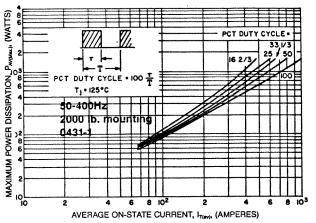
TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (JUNCTION TO CASE) TRANSIENT THERMAL IMPEDANCE, Zacon, ("C/WATT) MOUNTING 2000LB.MOUNTIN .01 11 TT Π ПП COOLED .00 .000 10-2 10-4 10-3 10-1 100 10 TIME, t, (SECONDS)

MAXIMUM ON-STATE POWER DISSIPATION (SINUSOIDAL WAVEFORM)



AVERAGE ON-STATE CURRENT, IT(av), (AMPERES)

MAXIMUM ON-STATE POWER DISSIPATION (RECTANGULAR WAVEFORM)

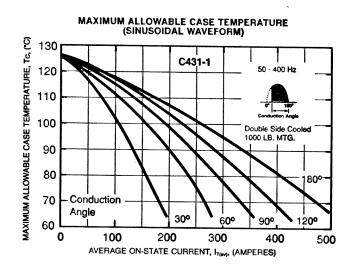




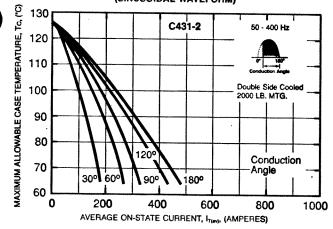
C431

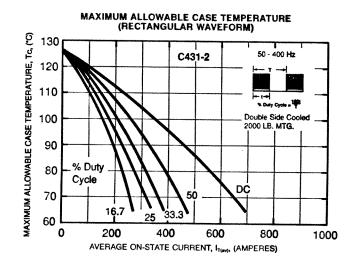
Phase Control SCR

450-600 Amperes Avg/500-1800 Volts

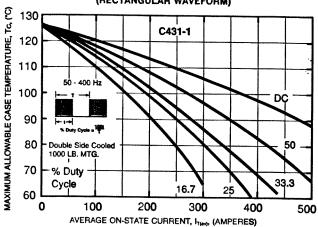


MAXIMUM ALLOWABLE CASE TEMPERATURE (SINUSOIDAL WAVEFORM)

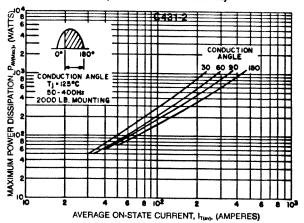




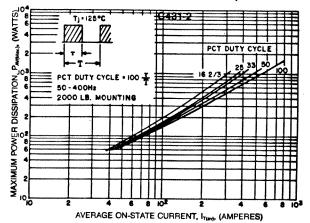
MAXIMUM ALLOWABLE CASE TEMPERATURE (RECTANGULAR WAVEFORM)



MAXIMUM ON-STATE POWER DISSIPATION (SINUSOIDAL WAVEFORM)

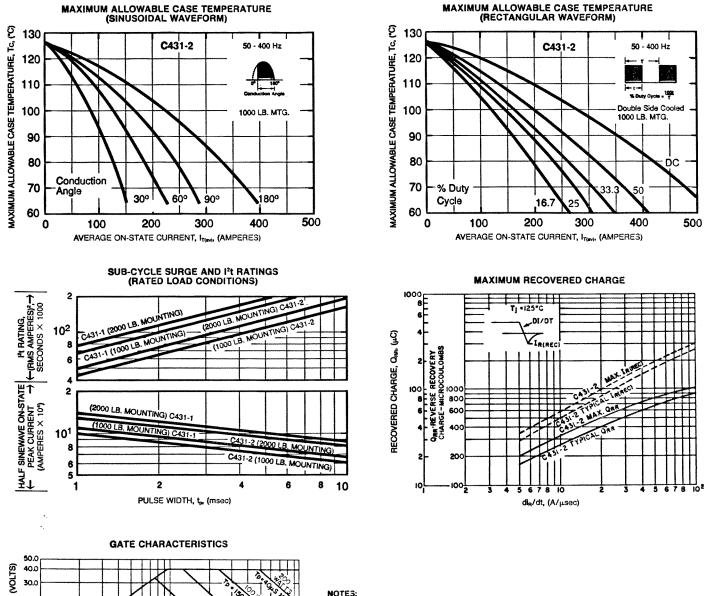


MAXIMUM ON-STATE POWER DISSIPATION (RECTANGULAR WAVEFORM)





C431 **Phase Control SCR** 450-600 Amperes Avg/500-1800 Volts



NOTES:

1. Maximum allowable average gate dissipation = 5 watts.

- 2. The locus of possible dc trigger points lie outside the boundaries shown at various case temperatures.
- 3. Tp = Rectangular gate current pulse width (5µs min. duration; 1.0µs max. rise time for 20V, 65 Ω source).
- 4. 20V 20 Ω is the minimum gate source load line when rate of circuit current rise >100 Amp/ μs or anode rate of current rise >200 Amps/ μs (Tp = 5 μs min., 0.5 μs max, rise time).

Maximum long-term repetitive anode di/dt = 500 Amps/µs with 20V - 20 Ω gate source.

POINTS

INE LOAD

.8 1.0

INSTANTANEOUS GATE CURRENT, Igt. (AMPERES)

20V - 20 Ω LOAD LINE

2.0 3.0 4.0 5.0 6.0 8.0 10

40

2017-200

. 4 .5 .6

POSSIBIÉ

RIC SER.

34

V_{GT}, 20.

> 10.0 8.0

6.0

5.0

4.0

3.0

2.0 150*

1.0

142

INSTANTANEOUS GATE VOLTAGE,